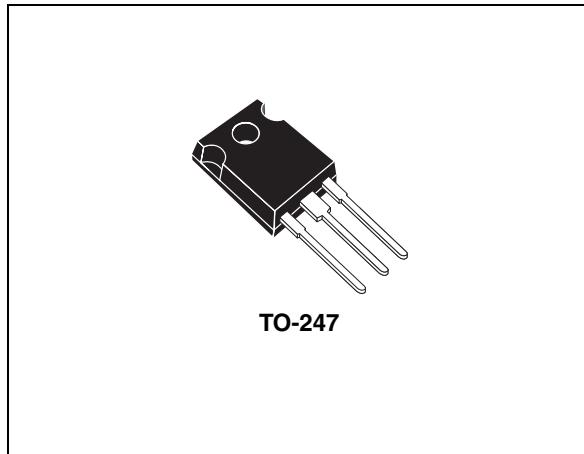


N-channel 900V - 0.40Ω - 15A - TO-247  
Zener - Protected SuperMESH™ PowerMOSFET

## General features

Type	$V_{DSS}$ (@ $T_{jmax}$ )	$R_{DS(on)}$	$I_D$	$P_W$
STW15NK90Z	900 V	< 0.55 Ω	15 A	350W

- Extremely high dv/dt capability
- 100% avalanche tested
- Gate charge minimized
- Very low intrinsic capacitances
- Very good manufacturing repeatability



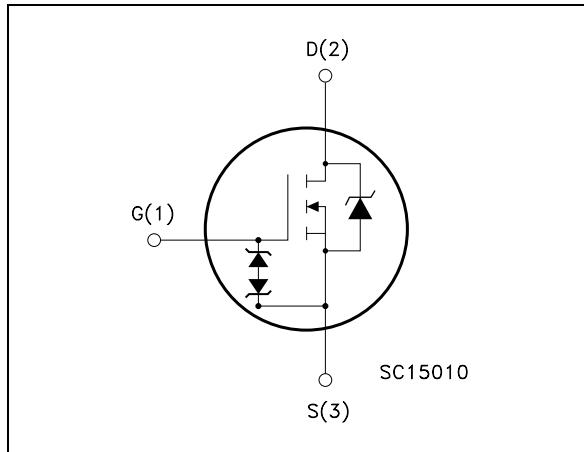
## Description

The SuperMESH™ series is obtained through an extreme optimization of ST's well established strip-based PowerMESH™ layout. In addition to pushing on-resistance significantly down, special care is taken to ensure a very good dv/dt capability for the most demanding applications. Such series complements ST full range of high voltage MOSFETs including revolutionary MDmesh™ products.

## Applications

- Switching application

## Internal schematic diagram



## Order codes

Part number	Marking	Package	Packaging
STW15NK90Z	W15NK90Z	TO-247	Tube

## Contents

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# 1 Electrical ratings

**Table 1. Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{DS}$	Drain-source voltage ( $V_{GS} = 0$ )	900	V
$V_{DGR}$	Drain-gate voltage ( $R_{GS} = 20\text{K}\Omega$ )	900	V
$V_{GS}$	Gate-source voltage	$\pm 30$	V
$I_D$	Drain current (continuous) at $T_C = 25^\circ\text{C}$	15	A
$I_D$	Drain current (continuous) at $T_C = 100^\circ\text{C}$	9.5	A
$I_{DM}^{(1)}$	Drain current (pulsed)	60	A
$P_{TOT}$	Total dissipation at $T_C = 25^\circ\text{C}$	350	W
	Derating Factor	2.77	W/ $^\circ\text{C}$
$V_{ESD} (\text{G-S})$	Gate source ESD(HBM-C=100pF, R=1,5K $\Omega$ )	6000	V
$dv/dt^{(2)}$	Peak diode recovery voltage slope	4.5	V/ns
$T_J$ $T_{stg}$	Operating junction temperature Storage temperature	-55 to 150	$^\circ\text{C}$

1. Pulse width limited by safe operating area
2.  $I_{SD} \leq 15 \text{ A}$ ,  $di/dt \leq 200\text{A}/\mu\text{s}$ ,  $V_{DD} \leq 900 \text{ V}$ ,  $T_j \leq T_{JMAX}$

**Table 2. Thermal data**

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case Max	0.36	$^\circ\text{C}/\text{W}$
$R_{thj-a}$	Thermal resistance junction-ambient Max	50	$^\circ\text{C}/\text{W}$
$T_J$	Maximum lead temperature for soldering purpose	300	$^\circ\text{C}$

**Table 3. Avalanche characteristics**

Symbol	Parameter	Value	Unit
$I_{AR}$	Avalanche current, repetitive or not-repetitive (pulse width limited by $T_j$ Max)	15	A
$E_{AS}$	Single pulse avalanche energy (starting $T_j=25^\circ\text{C}$ , $I_d=I_{AR}$ , $V_{DD}=50\text{V}$ )	360	mJ

**Table 4. Gate-source zener diode**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$BV_{GSO}$	Gate-source breakdown voltage	$I_{GS} = \pm 1\text{mA}$ (Open Drain)	30			V

## 1.1 Protection features of gate-to-source zener diodes

The built-in back-to-back Zener diodes have specifically been designed to enhance not only the device's ESD capability, but also to make them safely absorb possible voltage transients that may occasionally be applied from gate to source. In this respect the Zener voltage is appropriate to achieve an efficient and cost-effective intervention to protect the device's integrity. These integrated Zener diodes thus avoid the usage of external components.

## 2 Electrical characteristics

( $T_{CASE}=25^\circ\text{C}$  unless otherwise specified)

**Table 5. On/off states**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 1\text{mA}$ , $V_{GS} = 0$	900			V
$I_{DSS}$	Zero gate voltage drain current ( $V_{GS} = 0$ )	$V_{DS} = \text{Max rating}$ , $V_{DS} = \text{Max rating}$ , $T_c = 125^\circ\text{C}$			1 50	$\mu\text{A}$ $\mu\text{A}$
$I_{GSS}$	Gate body leakage current ( $V_{GS} = 0$ )	$V_{GS} = \pm 20\text{V}$			$\pm 10$	$\mu\text{A}$
$V_{GS(\text{th})}$	Gate threshold voltage	$V_{DS} = V_{GS}$ , $I_D = 150\ \mu\text{A}$	3	3.75	4.5	V
$R_{DS(\text{on})}$	Static drain-source on resistance	$V_{GS} = 10\text{V}$ , $I_D = 7.5\ \text{A}$		0.40	0.55	$\Omega$

**Table 6. Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$g_{fs}^{(1)}$	Forward transconductance	$V_{DS} = 15\text{V}$ , $I_D = 7.5\ \text{A}$		15		S
$C_{iss}$ $C_{oss}$ $C_{rss}$	Input capacitance Output capacitance Reverse transfer capacitance	$V_{DS} = 25\text{V}$ , $f = 1\ \text{MHz}$ , $V_{GS} = 0$		6100 465 96		$\text{pF}$ $\text{pF}$ $\text{pF}$
$C_{osseq}^{(2)}$	Equivalent output capacitance	$V_{GS} = 0$ , $V_{DS} = 0\text{V}$ to $720\text{V}$		230		$\text{pF}$
$t_{d(on)}$ $t_r$ $t_{d(off)}$ $t_f$	Turn-on delay time Rise time Off-voltage rise time Fall time	$V_{DD} = 450\ \text{V}$ , $I_D = 7.5\ \text{A}$ , $R_G = 4.7\ \Omega$ , $V_{GS} = 10\text{V}$ (see <a href="#">Figure 16</a> )		42 27 135 35		ns ns ns ns
$Q_g$ $Q_{gs}$ $Q_{gd}$	Total gate charge Gate-source charge Gate-drain charge	$V_{DD} = 720\text{V}$ , $I_D = 15\ \text{A}$ $V_{GS} = 10\text{V}$		190 56 70	256	nC nC nC

1. Pulsed: pulse duration=300 $\mu\text{s}$ , duty cycle 1.5%
2.  $C_{oss\text{ eq.}}$  is defined as a constant equivalent capacitance giving the same charging time as  $C_{oss}$  when  $V_{DS}$  increases from 0 to 80%  $V_{DSS}$

**Table 7. Source drain diode**

Symbol	Parameter	Test conditions	Min	Typ.	Max	Unit
$I_{SD}$	Source-drain current				15	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)				60	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD}=15A, V_{GS}=0$			1.6	V
$t_{rr}$ $Q_{rr}$ $I_{RRM}$	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_{SD}=15 A,$ $di/dt = 100A/\mu s,$ $V_{DD}=100 V, T_j=25^\circ C$ (see <a href="#">Figure 18</a> )		748 10.5 28		ns $\mu C$ A
$t_{rr}$ $Q_{rr}$ $I_{RRM}$	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_{SD}=15 A,$ $di/dt = 100A/\mu s,$ $V_{DD}=100V, T_j=150^\circ C$ (see <a href="#">Figure 18</a> )		900 13 28.5		ns $\mu C$ A

1. Pulse width limited by safe operating area
2. Pulsed: pulse duration=300 $\mu s$ , duty cycle 1.5%

## 2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

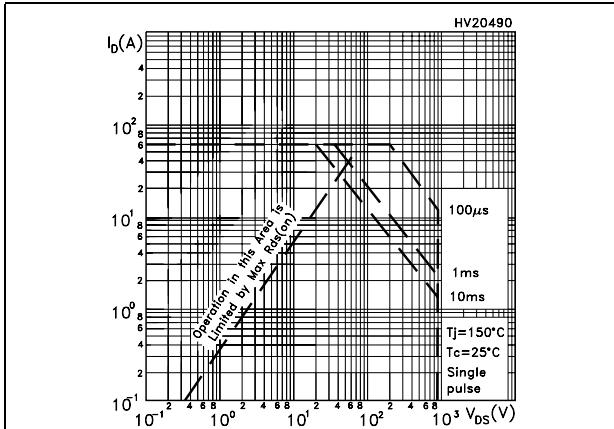


Figure 2. Thermal impedance

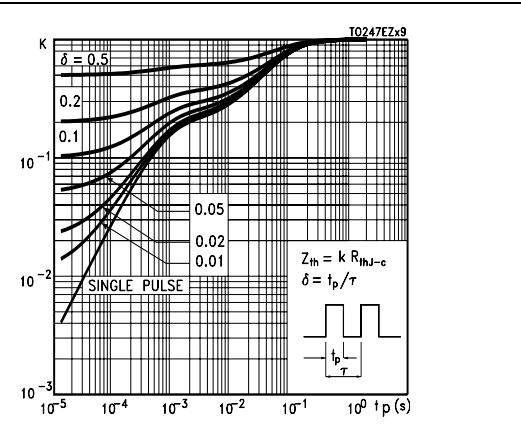


Figure 3. Output characteristics

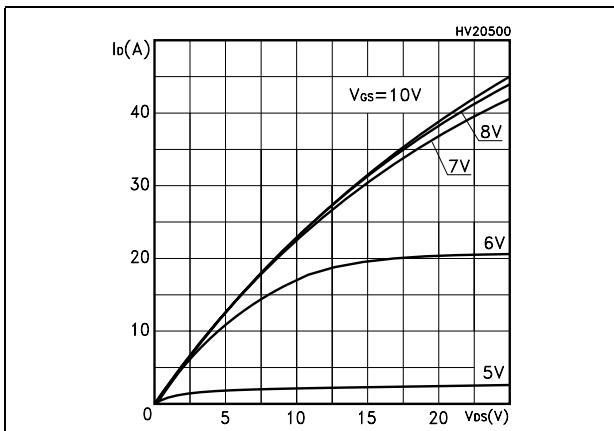


Figure 4. Transfer characteristics

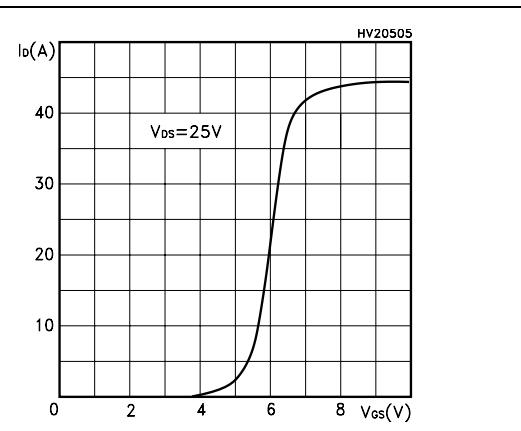


Figure 5. Transconductance

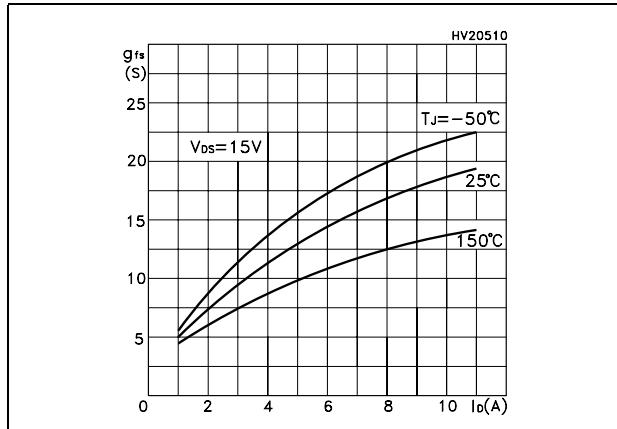


Figure 6. Static drain-source on resistance

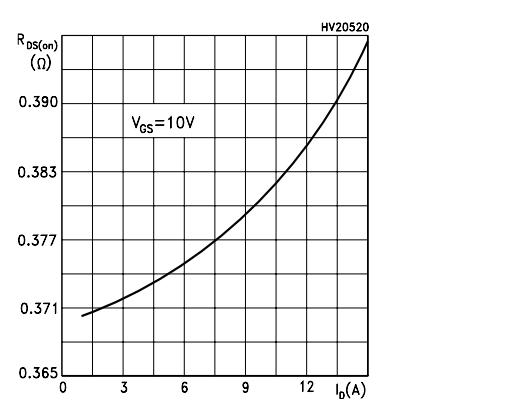


Figure 7. Gate charge vs gate-source voltage

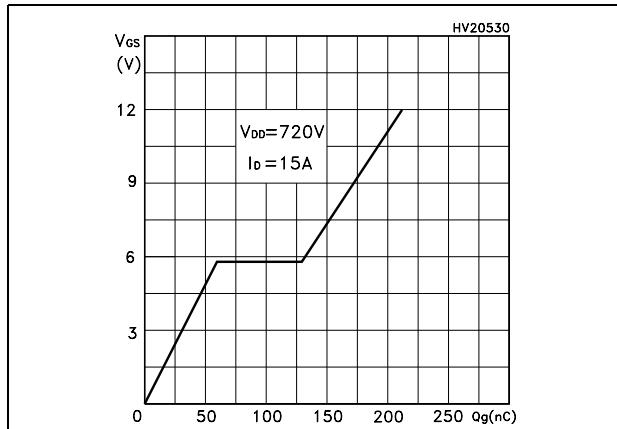


Figure 8. Capacitance variations

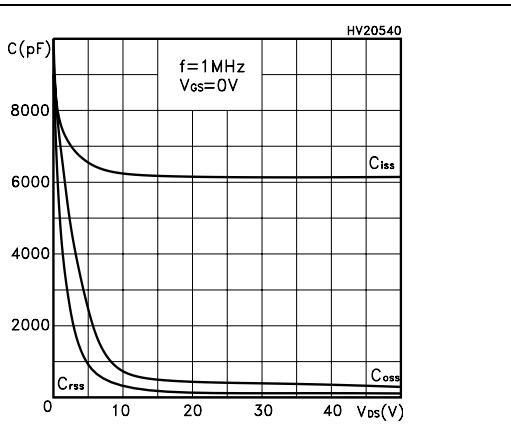


Figure 9. Normalized gate threshold voltage vs temperature

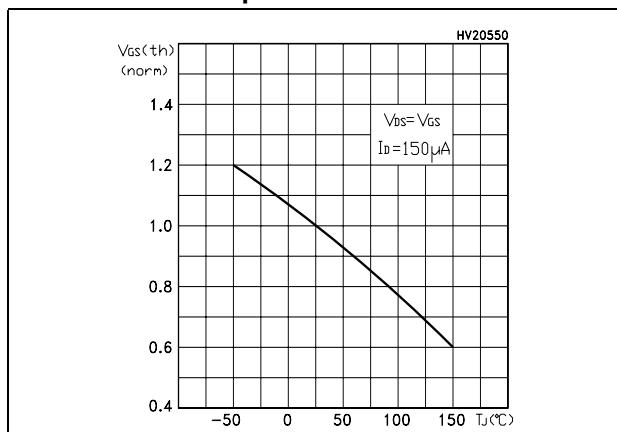
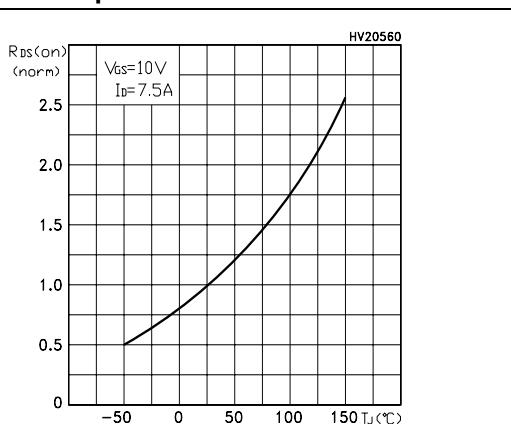
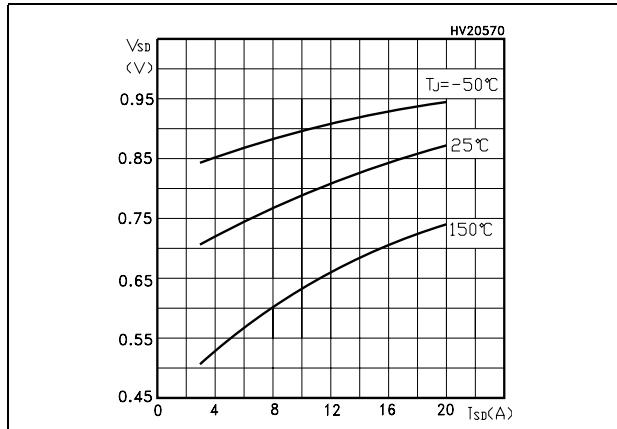


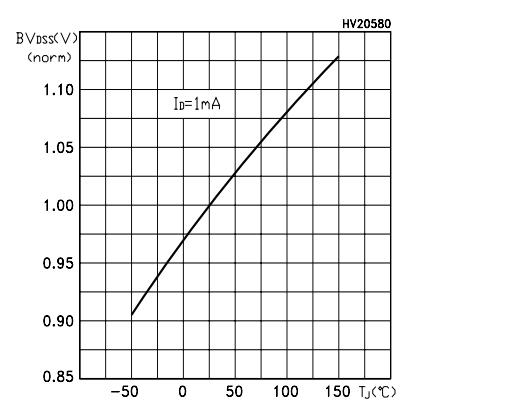
Figure 10. Normalized on resistance vs temperature



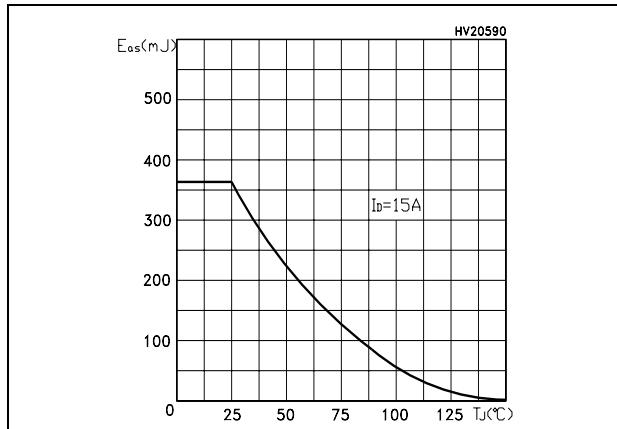
**Figure 11. Source-drain diode forward characteristics**



**Figure 12. Normalized  $B_{VDSS}$  vs temperature**

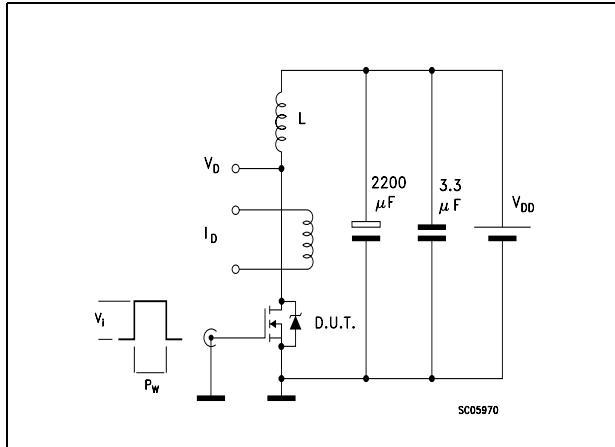


**Figure 13. Maximum avalanche energy vs temperature**

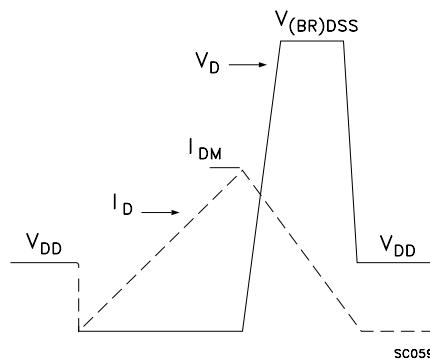


### 3 Test circuit Package mechanical data

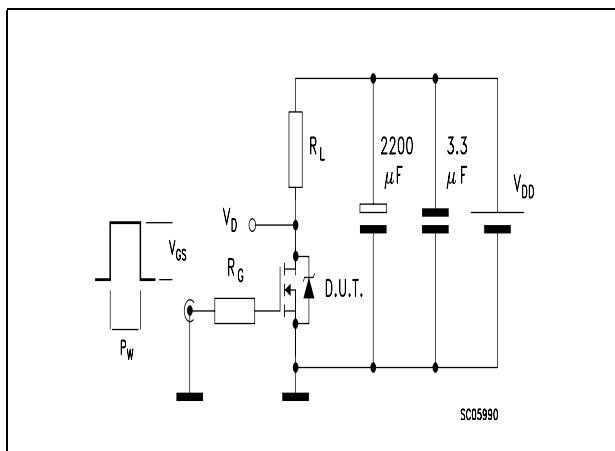
**Figure 14. Unclamped Inductive load test circuit**



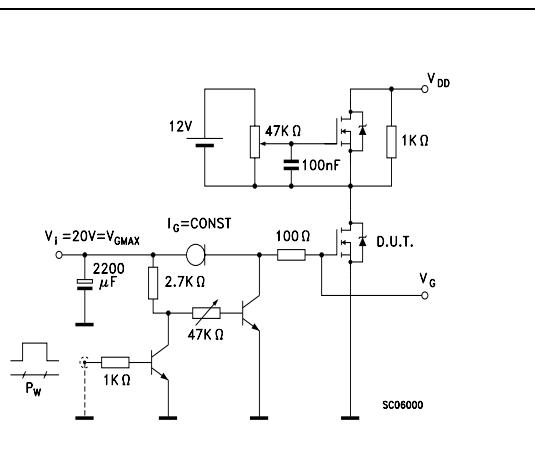
**Figure 15. Unclamped Inductive waveform**



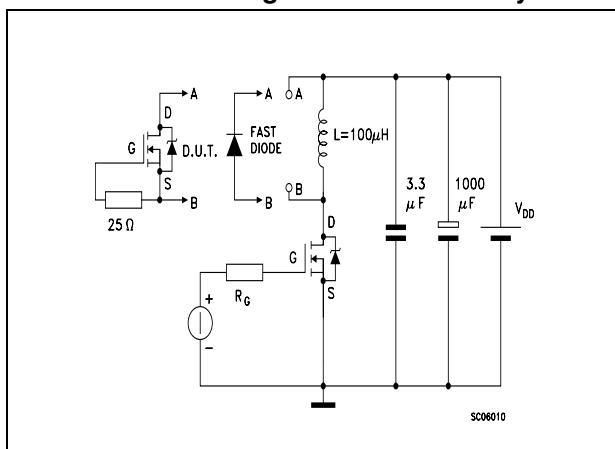
**Figure 16. Switching times test circuit for resistive load**



**Figure 17. Gate charge test circuit**



**Figure 18. Test circuit for inductive load switching and diode recovery times**

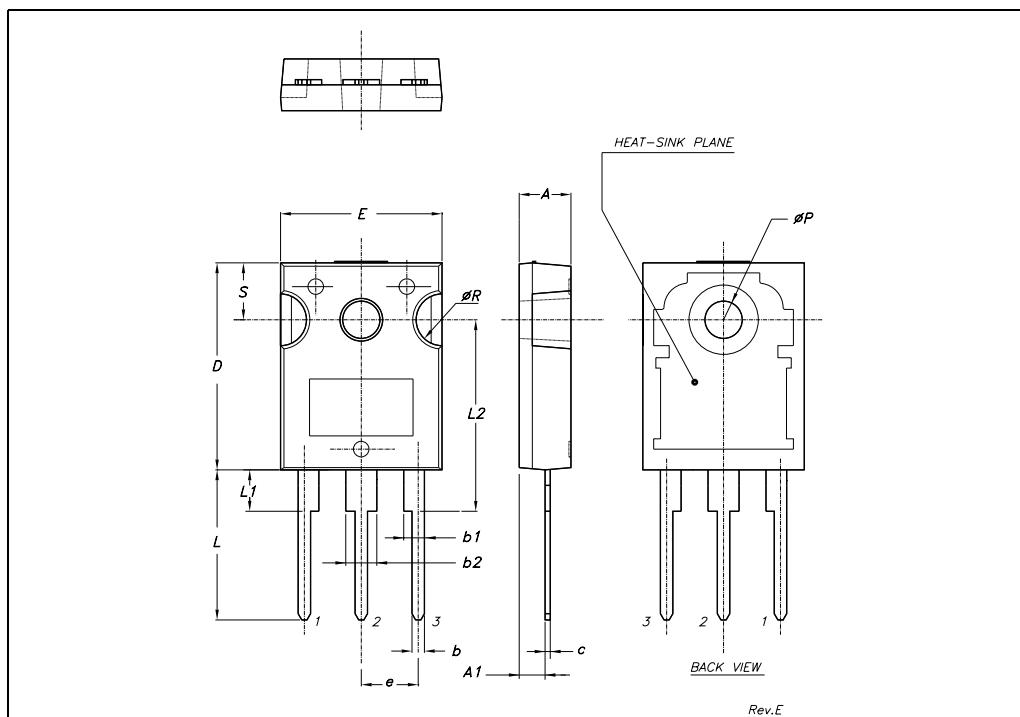


## 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: [www.st.com](http://www.st.com)

## TO-247 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.85		5.15	0.19		0.20
A1	2.20		2.60	0.086		0.102
b	1.0		1.40	0.039		0.055
b1	2.0		2.40	0.079		0.094
b2	3.0		3.40	0.118		0.134
c	0.40		0.80	0.015		0.03
D	19.85		20.15	0.781		0.793
E	15.45		15.75	0.608		0.620
e		5.45			0.214	
L	14.20		14.80	0.560		0.582
L1	3.70		4.30	0.14		0.17
L2		18.50			0.728	
$\phi P$	3.55		3.65	0.140		0.143
$\phi R$	4.50		5.50	0.177		0.216
S		5.50			0.216	



## 5 Revision history

**Table 8. Revision history**

Date	Revision	Changes
09-Sep-2004	1	Preliminary
08-Sep-2005	2	Complete datasheet
31-Jul-2005	3	New template, no content change

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